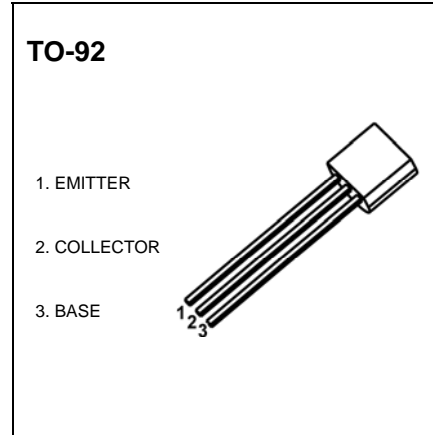


## TO-92 Plastic-Encapsulate Transistors

**2SA562** TRANSISTOR (PNP)

### FEATURES

- Excellent  $h_{FE}$  Linearity



### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-35	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-500	mA
$P_C$	Collector Power Dissipation	500	mW
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C = -1\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6\text{V}, I_E = 0, f = 1\text{MHz}$		13		pF

### CLASSIFICATION OF $h_{FE}$

RANK	O	Y
RANGE	70-140	120-240

# Typical Characteristics

# 2SA562

